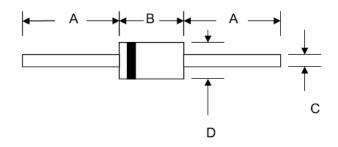


Technical Data
Data Sheet N0551, Rev. Features

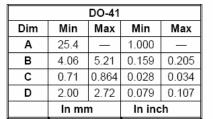
Green Products

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Part Name, SSG and Date Code



Marking Diagram:

Where XXXXX is YYWWL



BY133 = Part Name SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping
BY133	DO-41 (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

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Technical Data Data Sheet N0551, Rev. - **Green Products**

Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	BY133	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	1300	٧
RMS Reverse Voltage	VR(RMS)	910	V
Average Rectified Output Current (Note 1) @T _A = 75	°C Io	1.0	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30	А
Forward Voltage @I _F = 1.0	A VFM	1.0	V
Peak Reverse Current @T _A = 25° At Rated DC Blocking Voltage @T _A = 100°	I IDM	5.0 50	μА
Typical Junction Capacitance (Note 2)	Cj	15	pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R_{θ} JA	50	K/W
Operating Temperature Range	Tj	-65 to +125	°C
Storage Temperature Range	Тѕтс	-65 to +150	°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

^{2.} Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

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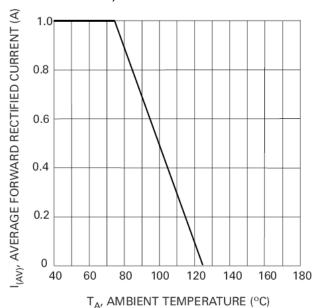


Fig. 1 Forward Current Derating Curve

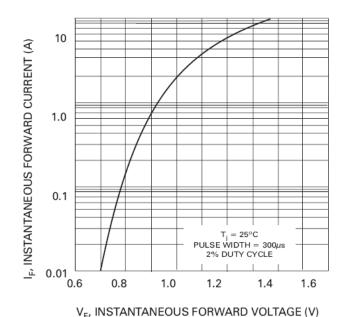


Fig. 2 Typical Forward Characteristics

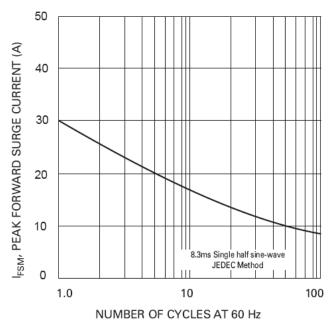


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

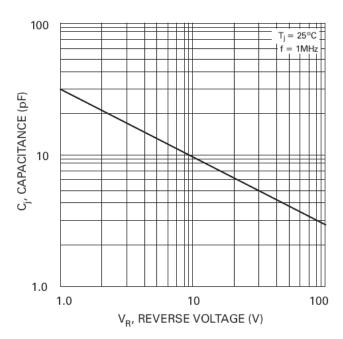


Fig. 4 Typical Junction Capacitance

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BY133 1.0 SILICON RECTIFIER

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